

## 16-Mbit (1M x 16) Static RAM

### Features

- TSOP I Configurable as 1M x 16 or as 2M x 8 SRAM
- Very high speed: 45 ns
- Wide voltage range: 2.2V – 3.6V
- Ultra-low active power
  - Typical active current: 2 mA @ f = 1 MHz
  - Typical active current: 18.5 mA @ f = f<sub>Max</sub> (45 ns speed)
- Ultra-low standby power
- Easy memory expansion with  $\overline{CE}_1$ ,  $\overline{CE}_2$  and  $\overline{OE}$  features
- Automatic power-down when deselected
- CMOS for optimum speed/power
- Available in Pb-free and non Pb-free 48-ball VFBGA and 48-pin TSOP I package

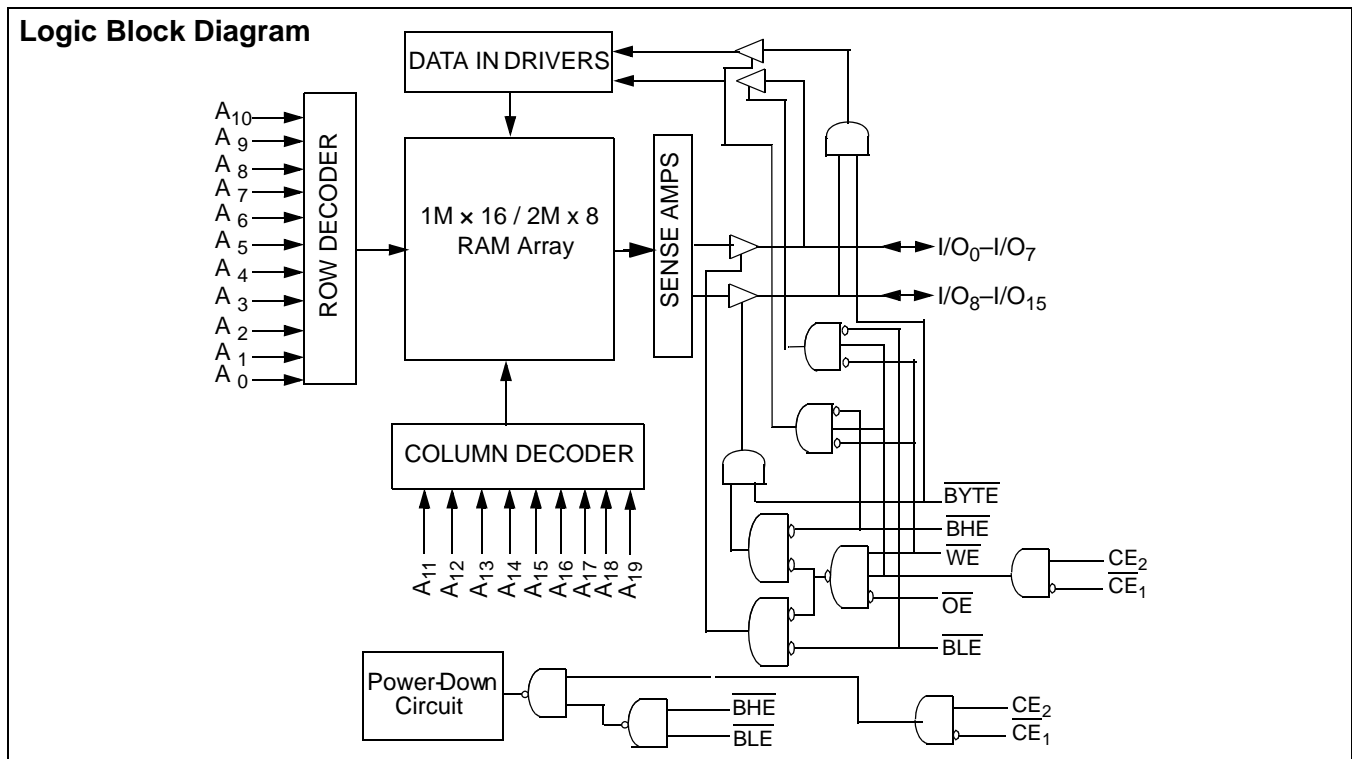
### Functional Description<sup>[1]</sup>

The CY62167DV30 is a high-performance CMOS static RAM organized as 1M words by 16 bits. This device features advanced circuit design to provide ultra-low active current. This is ideal for providing More Battery Life™ (MoBL®) in portable applications such as cellular telephones. The device

also has an automatic power-down feature that significantly reduces power consumption by 99% when addresses are not toggling. The device can also be put into standby mode when deselected ( $\overline{CE}_1$  HIGH or  $\overline{CE}_2$  LOW or both BHE and BLE are HIGH). The input/output pins (I/O<sub>0</sub> through I/O<sub>15</sub>) are placed in a high-impedance state when: deselected ( $\overline{CE}_1$  HIGH or  $\overline{CE}_2$  LOW), outputs are disabled ( $\overline{OE}$  HIGH), both Byte High Enable and Byte Low Enable are disabled (BHE, BLE HIGH), or during a Write operation ( $\overline{CE}_1$  LOW,  $\overline{CE}_2$  HIGH and WE LOW).

Writing to the device is accomplished by taking Chip Enables ( $\overline{CE}_1$  LOW and  $\overline{CE}_2$  HIGH) and Write Enable (WE) input LOW. If Byte Low Enable (BLE) is LOW, then data from I/O pins (I/O<sub>0</sub> through I/O<sub>7</sub>), is written into the location specified on the address pins (A<sub>0</sub> through A<sub>19</sub>). If Byte High Enable (BHE) is LOW, then data from I/O pins (I/O<sub>8</sub> through I/O<sub>15</sub>) is written into the location specified on the address pins (A<sub>0</sub> through A<sub>19</sub>).

Reading from the device is accomplished by taking Chip Enables ( $\overline{CE}_1$  LOW and  $\overline{CE}_2$  HIGH) and Output Enable ( $\overline{OE}$ ) LOW while forcing the Write Enable (WE) HIGH. If Byte Low Enable (BLE) is LOW, then data from the memory location specified by the address pins will appear on I/O<sub>0</sub> to I/O<sub>7</sub>. If Byte High Enable (BHE) is LOW, then data from memory will appear on I/O<sub>8</sub> to I/O<sub>15</sub>. See the truth table at the back of this data sheet for a complete description of Read and Write modes.

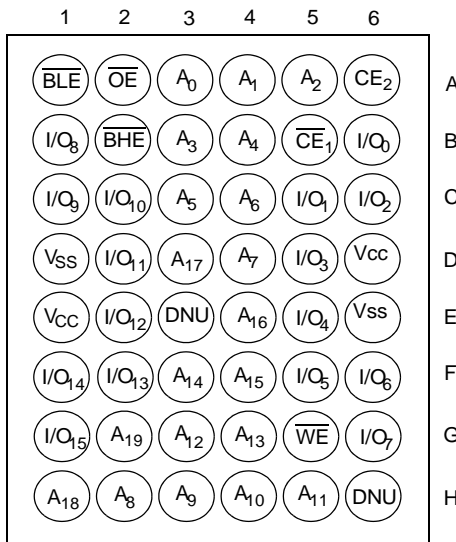
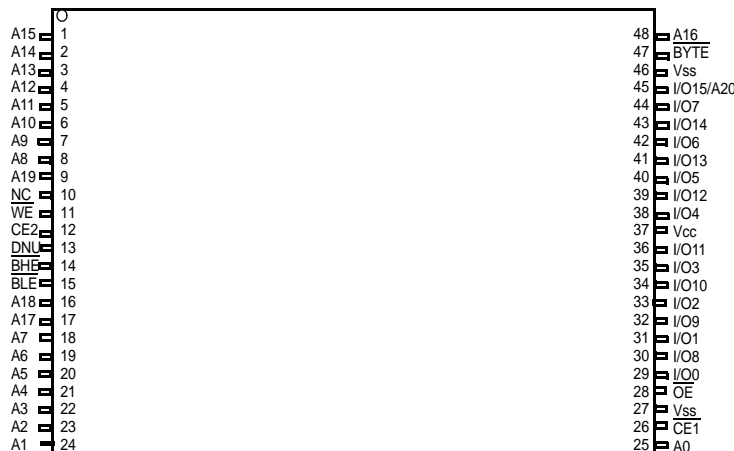


**Note:**

1. For best-practice recommendations, please refer to the Cypress application note "System Design Guidelines" on <http://www.cypress.com>.

**Product Portfolio**

Product	V <sub>CC</sub> Range (V)			Speed (ns)	Power Dissipation					
					Operating I <sub>CC</sub> (mA)				Standby I <sub>SB2</sub> ( $\mu$ A)	
	Min.	Typ. <sup>[2]</sup>	Max.		f = 1MHz		f = f <sub>Max</sub>			
					Typ. <sup>[2]</sup>	Max.	Typ. <sup>[2]</sup>	Max.	Typ. <sup>[2]</sup>	Max.
CY62167DV30LL	2.2	3.0	3.6	45	2	4	18.5	37	2.5	22
				55			15	30		
				70			12	25		

**Pin Configuration<sup>[3, 4, 5]</sup>**
**48-ball VFBGA**
**Top View**

**48-Pin TSOP I (Forward) (1M x 16/ 2M x 8)<sup>[6]</sup>**
**Top View**

**Notes:**

- Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at V<sub>CC</sub> = V<sub>CC(typ.)</sub>, T<sub>A</sub> = 25°C.
- NC pins are not connected on the die.
- DNU pins have to be left floating.
- Ball H6 for the FBGA package can be used to upgrade to a 32M density.
- The BYTE pin in the 48-TSOP I package has to be tied to V<sub>CC</sub> to use the device as a 1M X 16 SRAM. The 48-TSOP I package can also be used as a 2M X 8 SRAM by tying the BYTE signal to V<sub>SS</sub>. In the 2M x 8 configuration, Pin 45 is A20, while BHE, BLE and I/O8 to I/O14 pins are not used (DNU).

**Maximum Ratings**

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature ..... -65°C to +150°C

Ambient Temperature with Power Applied ..... -55°C to +125°C

Supply Voltage to Ground Potential ..... -0.2V to  $V_{CC} + 0.3V$

DC Voltage Applied to Outputs in High-Z State<sup>[7, 8]</sup> ..... -0.2V to  $V_{CC} + 0.3V$

DC Input Voltage<sup>[7, 8]</sup> ..... -0.2V to  $V_{CC} + 0.3V$

Output Current into Outputs (LOW) ..... 20 mA

Static Discharge Voltage ..... > 2001V (per MIL-STD-883, Method 3015)

Latch-up Current ..... > 200 mA

**Operating Range**

Device	Range	Ambient Temperature	$V_{CC}$ <sup>[9]</sup>
CY62167DV30LL	Industrial	-40°C to +85°C	2.20V to 3.60V

**Electrical Characteristics Over the Operating Range**

Parameter	Description	Test Conditions	CY62167DV30-45			CY62167DV30-55			CY62167DV30-70			Unit
			Min.	Typ. <sup>[2]</sup>	Max.	Min.	Typ. <sup>[2]</sup>	Max.	Min.	Typ. <sup>[2]</sup>	Max.	
$V_{OH}$	Output HIGH Voltage	$I_{OH} = -0.1 \text{ mA}$ , $V_{CC} = 2.20V$	2.0			2.0			2.0			V
		$I_{OH} = -1.0 \text{ mA}$ , $V_{CC} = 2.70V$	2.4			2.4			2.4			
$V_{OL}$	Output LOW Voltage	$I_{OL} = 0.1 \text{ mA}$ , $V_{CC} = 2.20V$			0.4			0.4			0.4	V
		$I_{OL} = 2.1 \text{ mA}$ , $V_{CC} = 2.70V$										
$V_{IH}$	Input HIGH Voltage	$V_{CC} = 2.2V \text{ to } 2.7V$	1.8		$V_{CC} + 0.3V$	1.8		$V_{CC} + 0.3V$	1.8		$V_{CC} + 0.3V$	V
		$V_{CC} = 2.7V \text{ to } 3.6V$	2.2			2.2			2.2			
$V_{IL}$	Input LOW Voltage	$V_{CC} = 2.2V \text{ to } 2.7V$	-0.3		0.6	-0.3		0.6	-0.3		0.6	V
		$V_{CC} = 2.7V \text{ to } 3.6V$			0.8			0.8			0.8	
$I_{IX}$	Input Leakage Current	$GND \leq V_I \leq V_{CC}$	-1		+1	-1		+1	-1		+1	$\mu\text{A}$
$I_{OZ}$	Output Leakage Current	$GND \leq V_O \leq V_{CC}$ , Output Disabled	-1		+1	-1		+1	-1		+1	$\mu\text{A}$
$I_{CC}$	$V_{CC}$ Operating Supply Current	$V_{CC} = V_{CC(max)}$ $I_{OUT} = 0 \text{ mA}$ CMOS levels $f = f_{Max} = 1/t_{RC}$ $f = 1 \text{ MHz}$	18.5	37		15	30		12	25		mA
			2	4		2	4		2	4		
$I_{SB1}$	Automatic CE Power-down Current — CMOS Inputs	$\overline{CE}_1 \geq V_{CC} - 0.2V$ or $CE_2 \leq 0.2V$ $V_{IN} \geq V_{CC} - 0.2V$ , $V_{IN} \leq 0.2V$ , $f = f_{Max}$ (Address and Data Only), $f = 0$ (OE, WE, BHE, BLE), $V_{CC} = 3.60V$		2.5	22		2.5	22		2.5	22	$\mu\text{A}$
$I_{SB2}$	Automatic CE Power-down Current — CMOS Inputs	$\overline{CE}_1 \geq V_{CC} - 0.2V$ or $CE_2 \leq 0.2V$ , $V_{IN} \geq V_{CC} - 0.2V$ or $V_{IN} \leq 0.2V$ , $f = 0$ , $V_{CC} = 3.60V$		2.5	22		2.5	22		2.5	22	$\mu\text{A}$

**Notes:**

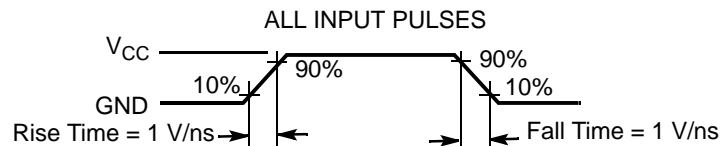
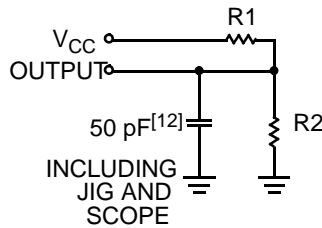
- $V_{IL(min.)} = -2.0V$  for pulse durations less than 20 ns.
- $V_{IH(max.)} = V_{CC} + 0.75V$  for pulse durations less than 20 ns.
- Full Device AC operation requires linear  $V_{CC}$  ramp from 0 to  $V_{CC(min.)}$  and  $V_{CC}$  must be stable at  $V_{CC(min.)}$  for 500  $\mu\text{s}$ .

**Capacitance<sup>[10, 11]</sup>**

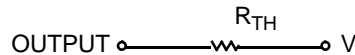
Parameter	Description	Test Conditions	Max.	Unit
C <sub>IN</sub>	Input Capacitance	T <sub>A</sub> = 25°C, f = 1 MHz, V <sub>CC</sub> = V <sub>CC(typ)</sub>	8	pF
C <sub>OUT</sub>	Output Capacitance		10	pF

**Thermal Resistance<sup>[10]</sup>**

Parameter	Description	Test Conditions	VFBGA	TSOP I	Unit
Θ <sub>JA</sub>	Thermal Resistance (Junction to Ambient)	Still Air, soldered on a 3 × 4.5 inch, 2-layer printed circuit board	55	60	°C/W
Θ <sub>JC</sub>	Thermal Resistance (Junction to Case)		16	4.3	°C/W

**AC Test Loads and Waveforms<sup>[12]</sup>**


Equivalent to: THEVENIN EQUIVALENT



Parameters	2.5V	3.0V	Unit
R1	16667	1103	Ω
R2	15385	1554	Ω
R <sub>TH</sub>	8000	645	Ω
V <sub>TH</sub>	1.20	1.75	V

**Data Retention Characteristics (Over the Operating Range)**

Parameter	Description	Conditions	Min.	Typ. <sup>[2]</sup>	Max.	Unit
V <sub>DR</sub>	V <sub>CC</sub> for Data Retention		1.5			V
I <sub>CCDR</sub>	Data Retention Current	V <sub>CC</sub> = 1.5V CE <sub>1</sub> ≥ V <sub>CC</sub> - 0.2V, CE <sub>2</sub> ≤ 0.2V, V <sub>IN</sub> ≥ V <sub>CC</sub> - 0.2V or V <sub>IN</sub> ≤ 0.2V			10	μA
t <sub>CDR</sub> <sup>[10]</sup>	Chip Deselect to Data Retention Time		0			ns
t <sub>R</sub> <sup>[13]</sup>	Operation Recovery Time		t <sub>RC</sub>			ns

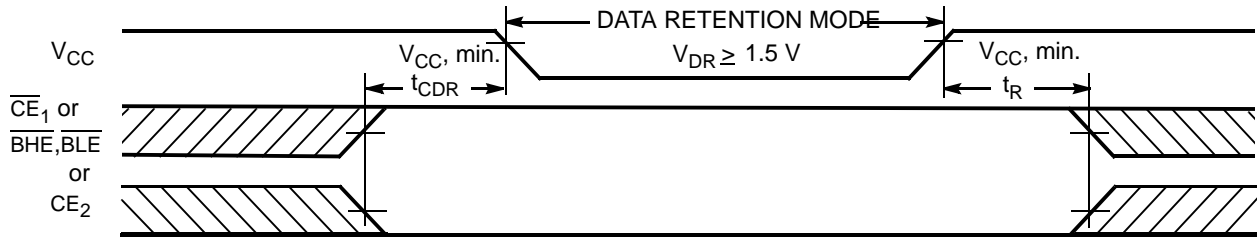
**Notes:**

10. Tested initially and after any design or process changes that may affect these parameters.

11. This applies for all packages.

12. Test condition for the 45 ns part is with a load capacitance of 30 pF.

 13. Full device operation requires linear V<sub>CC</sub> ramp from V<sub>DR</sub> to V<sub>CC(min.)</sub> ≥ 100 μs or stable at V<sub>CC(min.)</sub> ≥ 100 μs.

**Data Retention Waveform<sup>[14]</sup>**

**Switching Characteristics Over the Operating Range<sup>[15]</sup>**

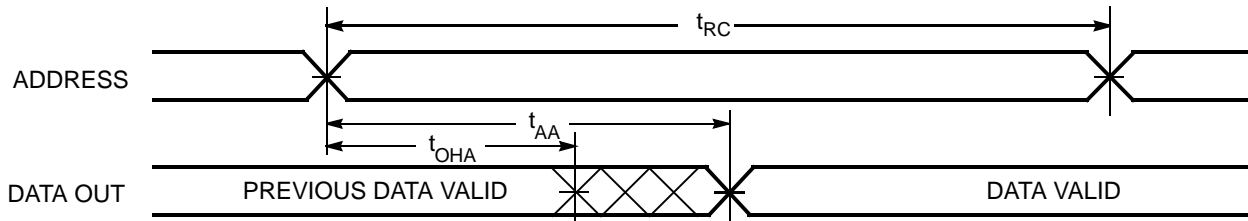
Parameter	Description	45 ns <sup>[12]</sup>		55 ns		70 ns		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	
<b>Read Cycle</b>								
$t_{RC}$	Read Cycle Time	45		55		70		ns
$t_{AA}$	Address to Data Valid		45		55		70	ns
$t_{OHA}$	Data Hold from Address Change	10		10		10		ns
$t_{ACE}$	$\overline{CE}_1$ LOW and $CE_2$ HIGH to Data Valid		45		55		70	ns
$t_{DOE}$	$\overline{OE}$ LOW to Data Valid		25		25		35	ns
$t_{LZOE}$	$\overline{OE}$ LOW to Low Z <sup>[16]</sup>	5		5		5		ns
$t_{HZOE}$	$\overline{OE}$ HIGH to High Z <sup>[16, 17]</sup>		15		20		25	ns
$t_{LZCE}$	$\overline{CE}_1$ LOW and $CE_2$ HIGH to Low Z <sup>[16]</sup>	10		10		10		ns
$t_{HZCE}$	$\overline{CE}_1$ HIGH and $CE_2$ LOW to High Z <sup>[16, 17]</sup>		20		20		25	ns
$t_{PU}$	$\overline{CE}_1$ LOW and $CE_2$ HIGH to Power-up	0		0		0		ns
$t_{PD}$	$\overline{CE}_1$ HIGH and $CE_2$ LOW to Power-down		45		55		70	ns
$t_{DBE}$	$\overline{BLE}/\overline{BHE}$ LOW to Data Valid		45		55		70	ns
$t_{LZBE}$	$\overline{BLE}/\overline{BHE}$ LOW to Low Z <sup>[16]</sup>	10		10		10		ns
$t_{HZBE}$	$\overline{BLE}/\overline{BHE}$ HIGH to HIGH Z <sup>[16, 17]</sup>		15		20		25	ns
<b>Write Cycle<sup>[18]</sup></b>								
$t_{WC}$	Write Cycle Time	45		55		70		ns
$t_{SCE}$	$\overline{CE}_1$ LOW and $CE_2$ HIGH to Write End	40		40		60		ns
$t_{AW}$	Address Set-Up to Write End	40		40		60		ns
$t_{HA}$	Address Hold from Write End	0		0		0		ns
$t_{SA}$	Address Set-Up to Write Start	0		0		0		ns
$t_{PWE}$	$\overline{WE}$ Pulse Width	35		40		45		ns
$t_{BW}$	$\overline{BLE}/\overline{BHE}$ LOW to Write End	40		40		60		ns
$t_{SD}$	Data Set-Up to Write End	25		25		30		ns
$t_{HD}$	Data Hold from Write End	0		0		0		ns
$t_{HZWE}$	$\overline{WE}$ LOW to High-Z <sup>[16, 17]</sup>		15		20		25	ns
$t_{LZWE}$	$\overline{WE}$ HIGH to Low-Z <sup>[16]</sup>	10		10		10		ns

**Notes:**

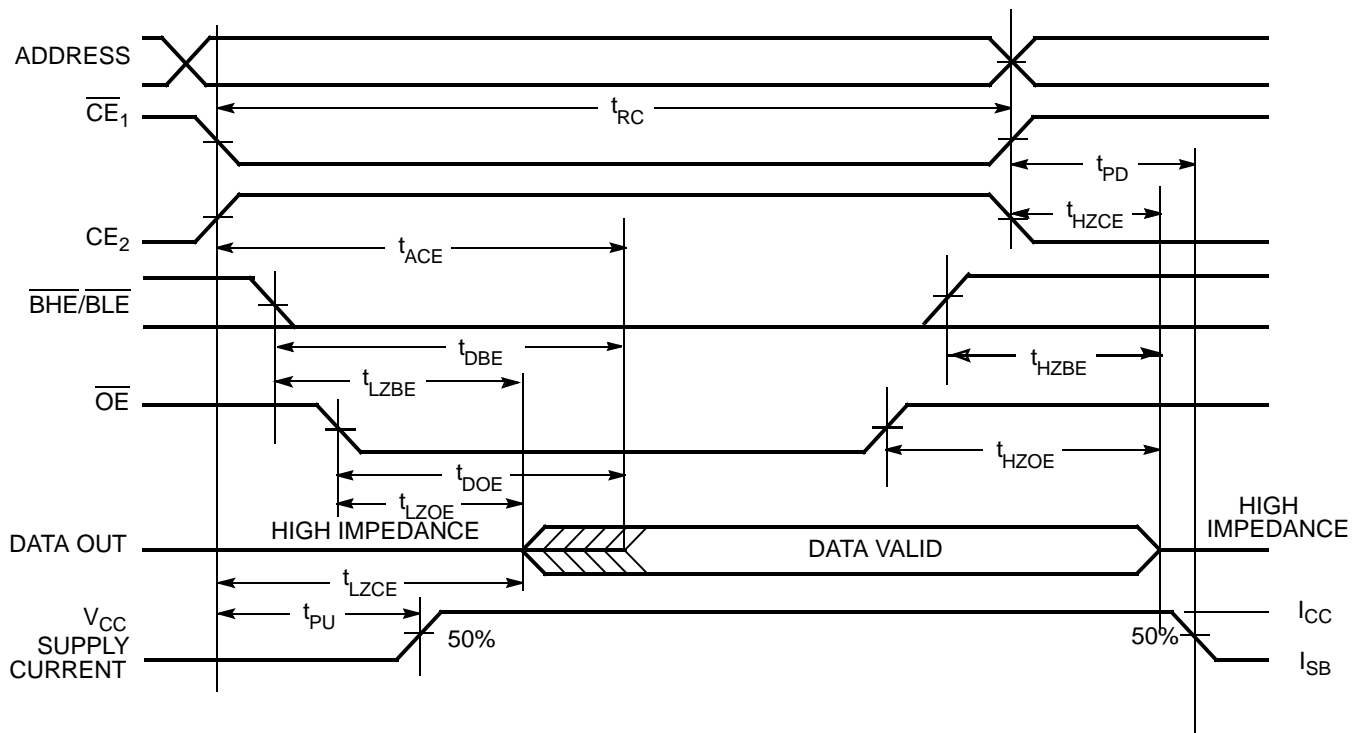
- $\overline{BHE}, \overline{BLE}$  is the AND of both  $\overline{BHE}$  and  $\overline{BLE}$ . Chip can be deselected by either disabling the chip enable signals or by disabling both  $\overline{BHE}$  and  $\overline{BLE}$ .
- Test conditions for all parameters other than Tri-state parameters assume signal transition time of 1 ns/V, timing reference levels of  $V_{CC(typ)}/2$ , input pulse levels of 0 to  $V_{CC(typ)}$ , and output loading of the specified  $I_{OL}/I_{OH}$  as shown in the "AC Test Loads and Waveforms" section.
- At any given temperature and voltage condition,  $t_{HZCE}$  is less than  $t_{LZCE}$ ,  $t_{HZBE}$  is less than  $t_{LZBE}$ ,  $t_{HZOE}$  is less than  $t_{LZOE}$ , and  $t_{HZWE}$  is less than  $t_{LZWE}$  for any given device.
- $t_{HZOE}$ ,  $t_{HZCE}$ ,  $t_{HZBE}$ , and  $t_{HZWE}$  transitions are measured when the outputs enter a high impedance state.
- The internal Write time of the memory is defined by the overlap of  $\overline{WE}$ ,  $CE_1 = V_{IL}$ ,  $\overline{BHE}$  and/or  $\overline{BLE} = V_{IL}$ , and  $CE_2 = V_{IH}$ . All signals must be ACTIVE to initiate a write and any of these signals can terminate a write by going INACTIVE. The data input set-up and hold timing should be referenced to the edge of the signal that terminates the Write.

### Switching Waveforms

#### Read Cycle 1 (Address Transition Controlled)<sup>[19, 20]</sup>



#### Read Cycle 2 ( $\overline{OE}$ Controlled)<sup>[20, 21]</sup>

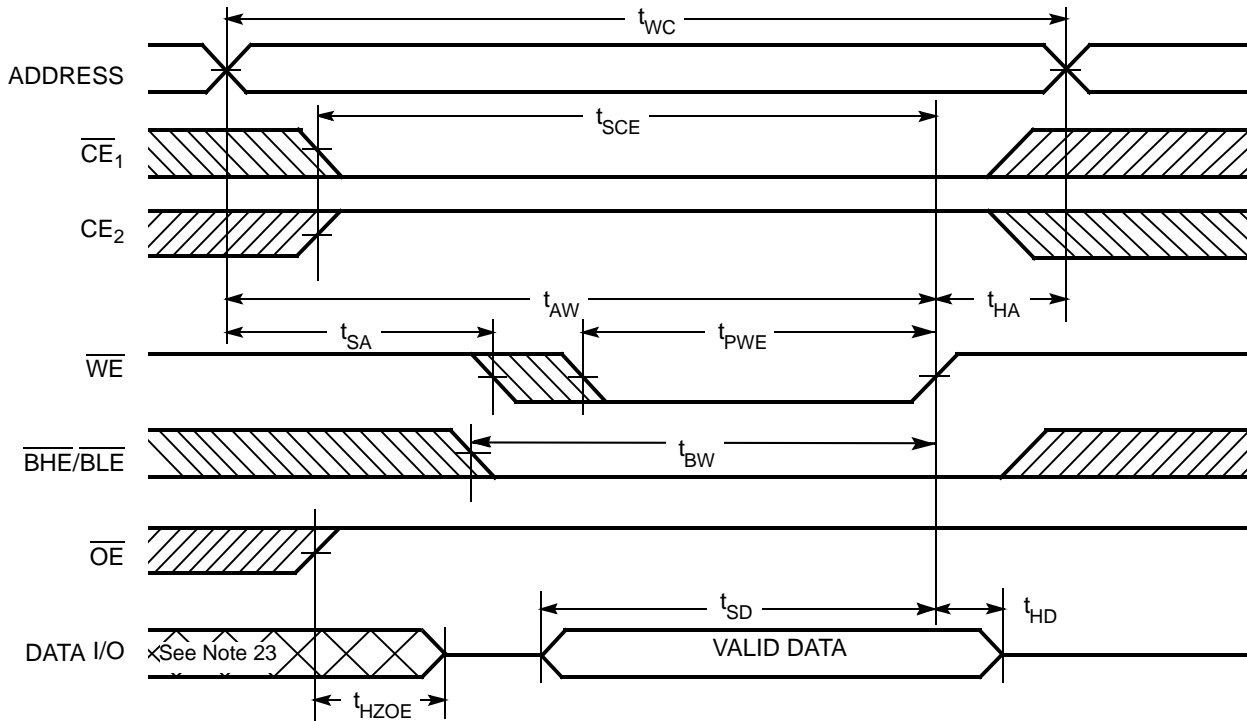


**Notes:**

- 19. The device is continuously selected.  $\overline{OE}$ ,  $\overline{CE}_1 = V_{IL}$ ,  $\overline{BHE}$  and/or  $\overline{BLE} = V_{IL}$ , and  $CE_2 = V_{IH}$ .
- 20.  $\overline{WE}$  is HIGH for read cycle.
- 21. Address valid prior to or coincident with  $\overline{CE}_1$ ,  $\overline{BHE}$ ,  $\overline{BLE}$  transition LOW and  $CE_2$  transition HIGH.

Switching Waveforms (continued)

Write Cycle 1 (WE Controlled)<sup>[18, 22, 23, 24]</sup>

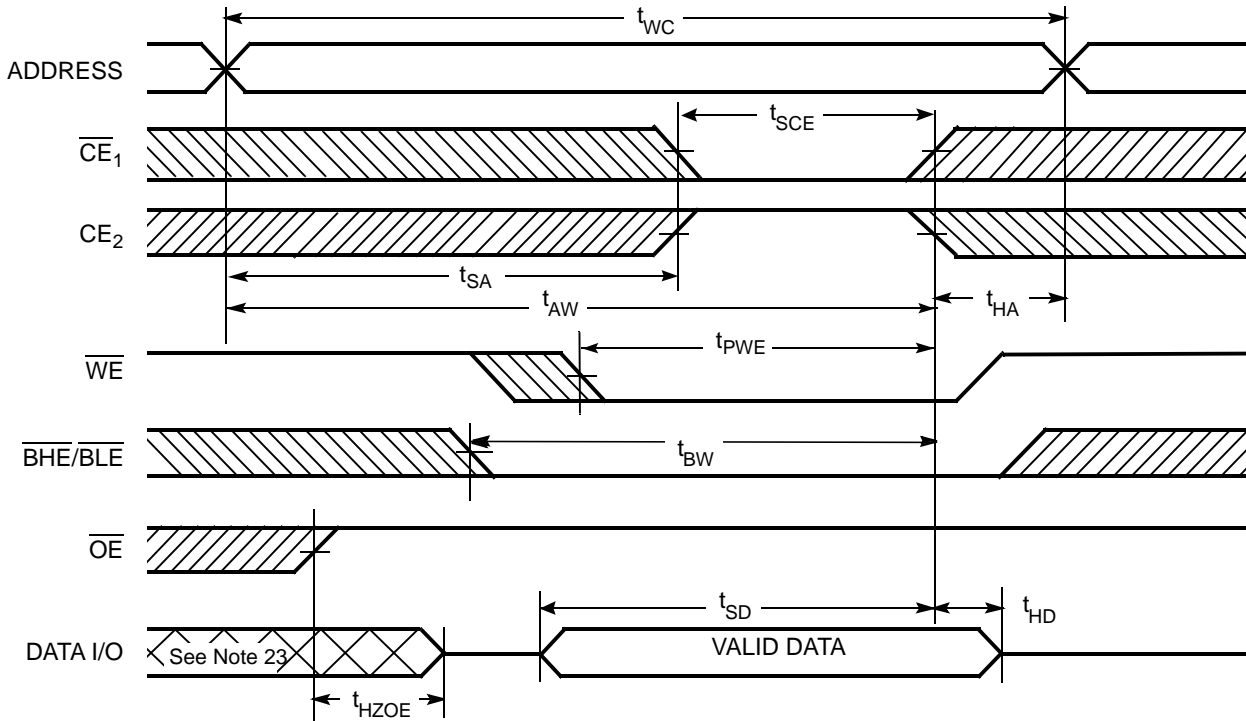


Notes:

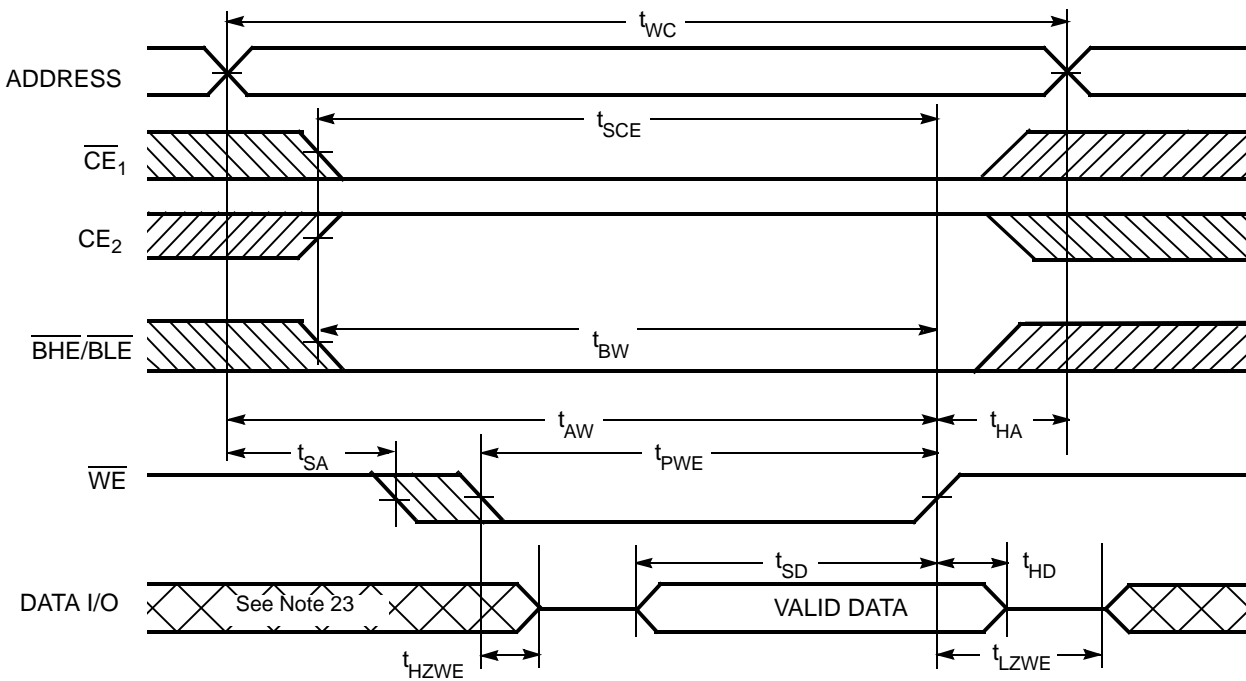
- 22. Data I/O is high-impedance if  $\overline{OE} = V_{IH}$ .
- 23. If CE<sub>1</sub> goes HIGH and CE<sub>2</sub> goes LOW simultaneously with  $\overline{WE} = V_{IH}$ , the output remains in a high-impedance state.
- 24. During this period, the I/Os are in output state and input signals should not be applied.

Switching Waveforms (continued)

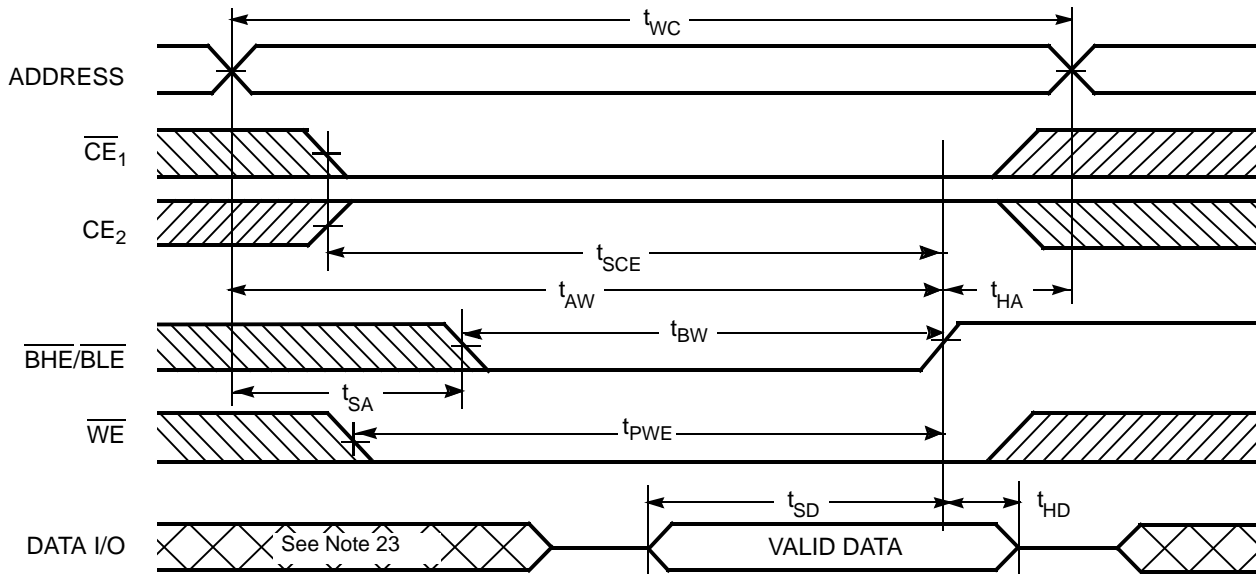
Write Cycle 2 ( $\overline{CE}_1$  or  $\overline{CE}_2$  Controlled)<sup>[18, 22, 23, 24]</sup>



Write Cycle 3 ( $\overline{WE}$  Controlled,  $\overline{OE}$  LOW)<sup>[23, 24]</sup>





**Switching Waveforms (continued)**
**Write Cycle 4 (BHE/BLE Controlled, OE LOW)<sup>[23, 24]</sup>**

**Truth Table**

$\overline{CE}_1$	$CE_2$	$\overline{WE}$	$\overline{OE}$	$\overline{BHE}$	$\overline{BLE}$	Inputs/Outputs	Mode	Power
H	X	X	X	X	X	High Z	Deselect/Power-Down	Standby ( $I_{SB}$ )
X	L	X	X	X	X	High Z	Deselect/Power-Down	Standby ( $I_{SB}$ )
X	X	X	X	H	H	High Z	Deselect/Power-Down	Standby ( $I_{SB}$ )
L	H	H	L	L	L	Data Out ( $I/O_0$ – $I/O_{15}$ )	Read	Active ( $I_{CC}$ )
L	H	H	L	H	L	High Z ( $I/O_8$ – $I/O_{15}$ ); Data Out ( $I/O_0$ – $I/O_7$ )	Read	Active ( $I_{CC}$ )
L	H	H	L	L	H	Data Out ( $I/O_8$ – $I/O_{15}$ ); High Z ( $I/O_0$ – $I/O_7$ )	Read	Active ( $I_{CC}$ )
L	H	L	X	L	L	Data In ( $I/O_0$ – $I/O_{15}$ )	Write	Active ( $I_{CC}$ )
L	H	L	X	H	L	High Z ( $I/O_8$ – $I/O_{15}$ ); Data In ( $I/O_0$ – $I/O_7$ )	Write	Active ( $I_{CC}$ )
L	H	L	X	L	H	Data In ( $I/O_8$ – $I/O_{15}$ ); High Z ( $I/O_0$ – $I/O_7$ )	Write	Active ( $I_{CC}$ )
L	H	H	H	L	H	High Z	Output Disabled	Active ( $I_{CC}$ )
L	H	H	H	H	L	High Z	Output Disabled	Active ( $I_{CC}$ )
L	H	H	H	L	L	High Z	Output Disabled	Active ( $I_{CC}$ )

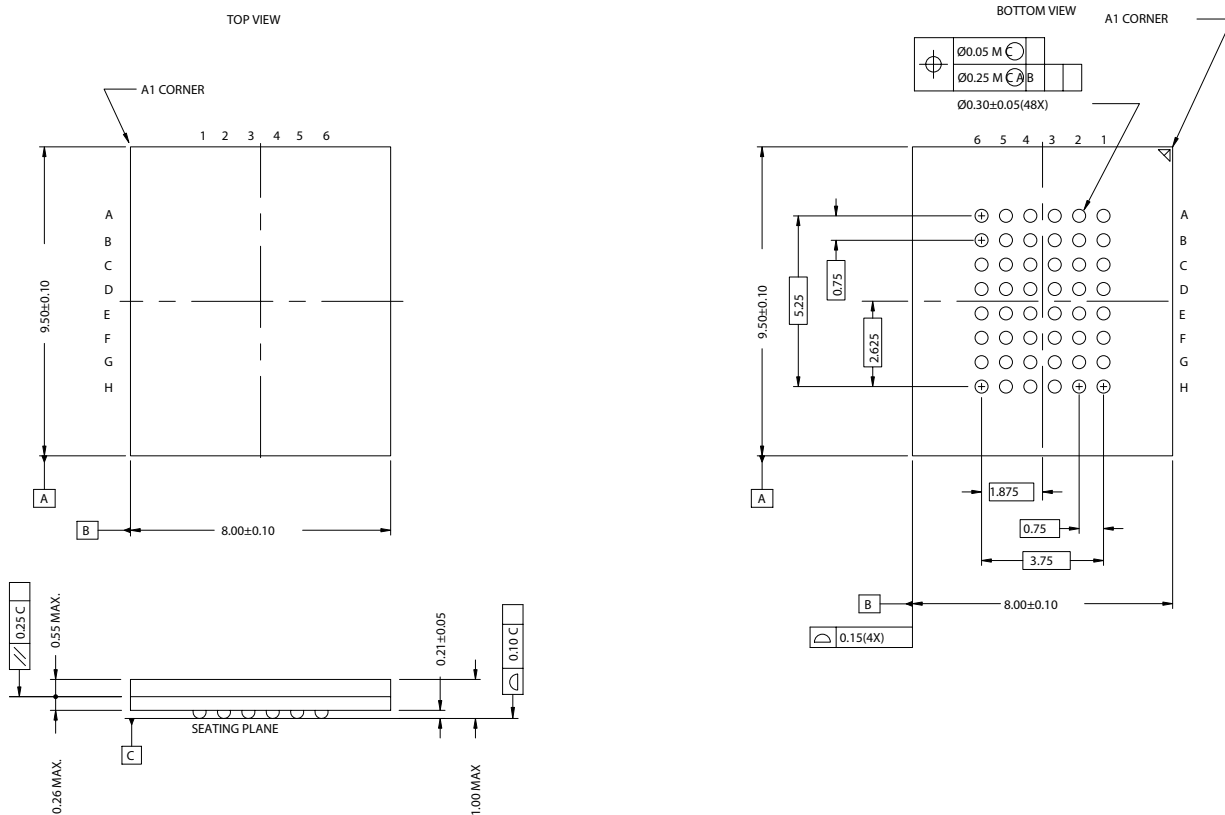
**Ordering Information**

Speed (ns)	Ordering Code	Package Diagram	Package Type	Operating Range
45	CY62167DV30LL-45ZXI	51-85183	48-pin TSOP I (12 x 18.4 x 1 mm) (Pb-free)	Industrial
55	CY62167DV30LL-55BVI	51-85178	48-ball Fine Pitch BGA (8 x 9.5 x 1 mm)	
	CY62167DV30LL-55BVXI		48-ball Fine Pitch BGA (8 x 9.5 x 1 mm) (Pb-free)	
	CY62167DV30LL-55ZI	51-85183	48-pin TSOP I (12 x 18.4 x 1 mm)	
	CY62167DV30LL-55ZXI		48-pin TSOP I (12 x 18.4 x 1 mm) (Pb-free)	
70	CY62167DV30LL-70BVI	51-85178	48-ball Fine Pitch BGA (8 x 9.5 x 1 mm)	

Please contact your local Cypress sales representative for availability of these parts

**Package Diagrams**

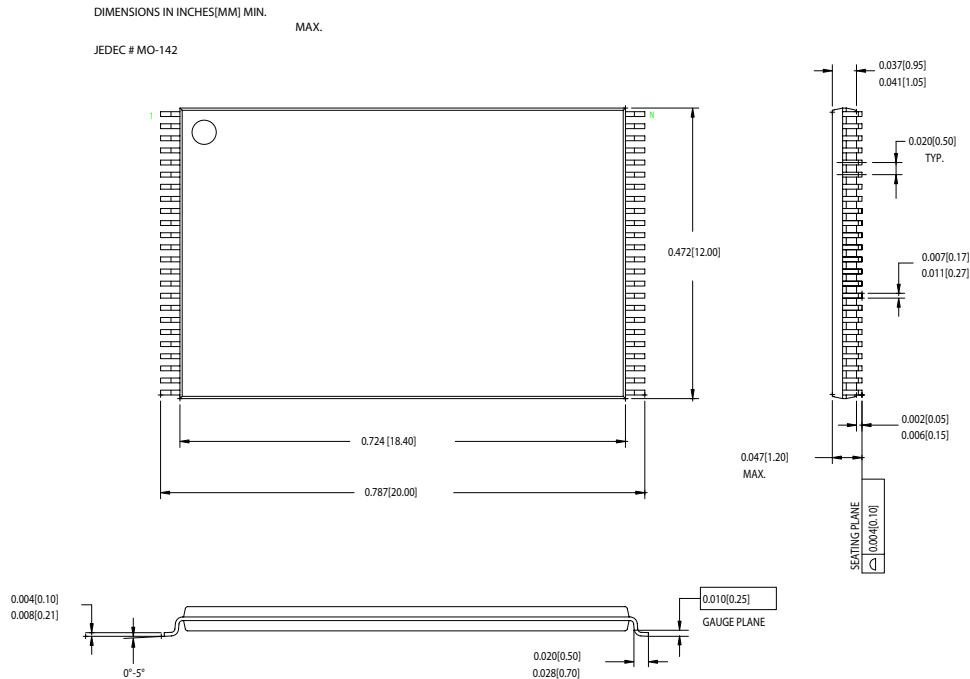
**48-ball VFBGA (8 x 9.5 x 1 mm) (51-85178)**



51-85178-\*\*

Package Diagrams (continued)

48-pin TSOP I (12 x 18.4 x 1mm) (51-85183)



51-85183-A

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**Document History Page**

Document Title: CY62167DV30 MoBL®, 16-Mbit (1M x 16) Static RAM Document Number: 38-05328				
REV.	ECN NO.	Issue Date	Orig. of Change	Description of Change
**	118408	09/30/02	GUG	New Data Sheet
*A	123692	02/11/03	DPM	Changed Advanced to Preliminary Added package diagram
*B	126555	04/25/03	DPM	Minor change: Changed Sunset Owner from DPM to HRT
*C	127841	09/10/03	XRJ	Added 48 TSOP I package
*D	205701		AJU	Changed BYTE pin usage description for 48 TSOPI package
*E	238050	See ECN	KKV/AJU	Replaced 48-ball VFBGA package diagram; Modified Package Name in Ordering Information table from BV48A to BV48B
*F	304054	See ECN	PCI	Added 45-ns Speed Bin in AC, DC and Ordering Information tables Added Footnote #12 on page #4 Added Pb-free packages on page # 10
*G	492895	See ECN	VKN	Modified datasheet to explain x8 configurability Removed L power bin from the product offering Updated Ordering Information Table